


# BCR3AS

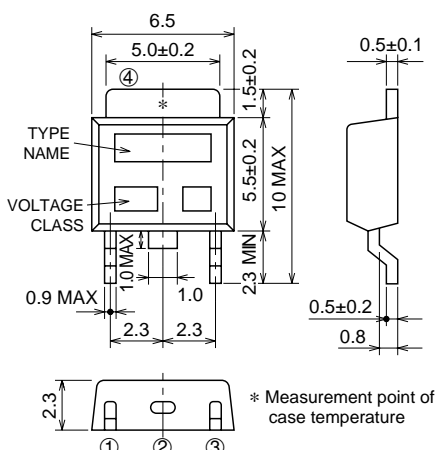
LOW POWER USE  
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

**BCR3AS**



- **IT (RMS)** ..... **3A**
- **VDRM** ..... **400V/600V**
- **IFGT I , IRGT I , IRGT III** ..... **15mA (10mA) \*2**

**OUTLINE DRAWING** Dimensions in mm



\* Measurement point of case temperature

① T1 TERMINAL  
② T2 TERMINAL  
③ GATE TERMINAL  
④ T2 TERMINAL

MP-3

**APPLICATION**

Hybrid IC, solid state relay, switching mode power supply, light dimmer, electric fan, electric blankets, control of household equipment such as washing machine, other general purpose control applications

**MAXIMUM RATINGS**

Symbol	Parameter	Voltage class		Unit
		8	12	
VDRM	Repetitive peak off-state voltage *1	400	600	V
VDSM	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=108°C	3	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	30	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	3.7	A <sup>2</sup> s
PGM	Peak gate power dissipation		3	W
PG (AV)	Average gate power dissipation		0.3	W
VGM	Peak gate voltage		6	V
IGM	Peak gate current		0.3	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	0.26	g

\*1. Gate open.

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## ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	T <sub>j</sub> =125°C, V <sub>DRM</sub> applied	—	—	2.0	mA	
VTM	On-state voltage	T <sub>c</sub> =25°C, I <sub>TM</sub> =4.5A, Instantaneous measurement	—	—	1.7	V	
VFGT I	Gate trigger voltage *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	1.5	V
VRGT I			II	—	—	1.5	V
VRGT III			III	—	—	1.5	V
IFGT I	Gate trigger current *2	T <sub>j</sub> =25°C, V <sub>D</sub> =6V, R <sub>L</sub> =6Ω, R <sub>G</sub> =330Ω	I	—	—	15*2	mA
IRGT I			II	—	—	15*2	mA
IRGT III			III	—	—	15*2	mA
VGD	Gate non-trigger voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.2	—	—	V	
Rth (j-c)	Thermal resistance	Junction to case *4	—	—	3.8	°C/W	
(dv/dt) <sub>c</sub>	Critical-rate of rise of off-state commutating voltage		*3	—	—	V/μs	

\*2. High sensitivity (I<sub>GT</sub>≤10mA) is also available.

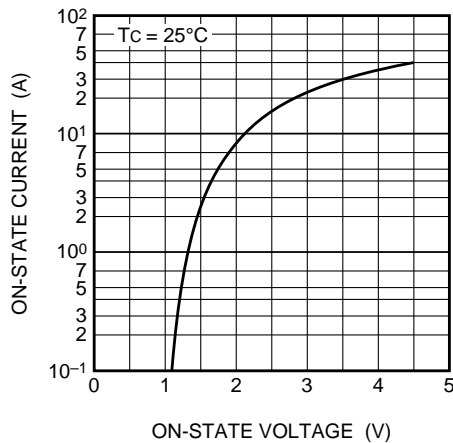
\*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.

\*4. Case temperature is measured on the T<sub>2</sub> terminal.

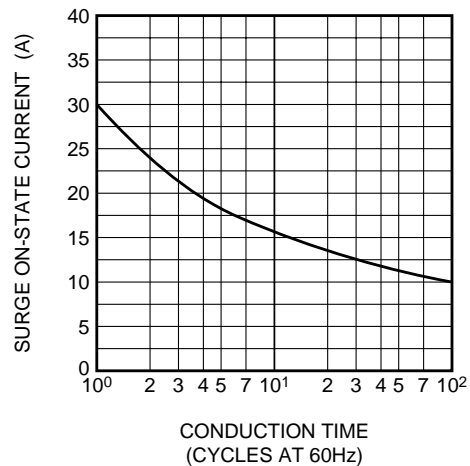
Voltage class	V <sub>DRM</sub> (V)	(dv/dt) <sub>c</sub>		Test conditions	Commutating voltage and current waveforms (inductive load)
		Min.	Unit		
8	400	5	V/μs	1. Junction temperature T <sub>j</sub> =125°C 2. Rate of decay of on-state commutating current (di/dt) <sub>c</sub> =-1.5A/ms 3. Peak off-state voltage V <sub>D</sub> =400V	
12	600				

## PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS

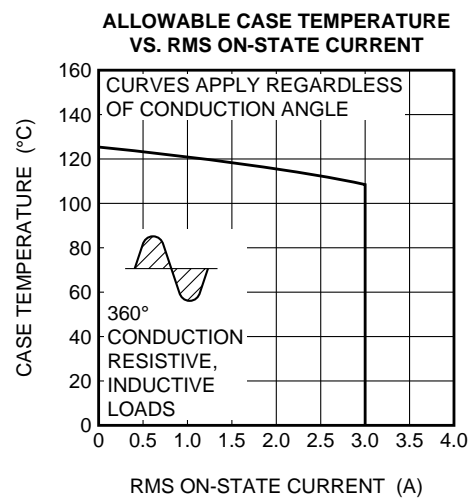
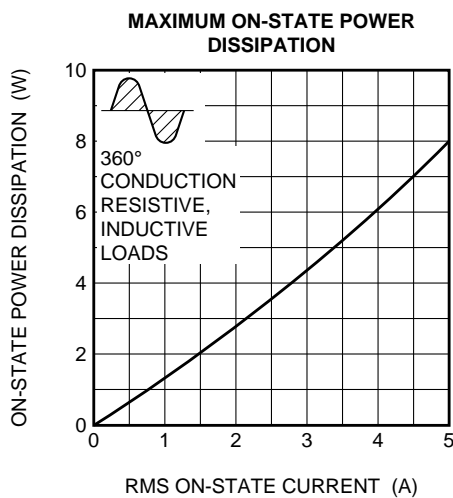
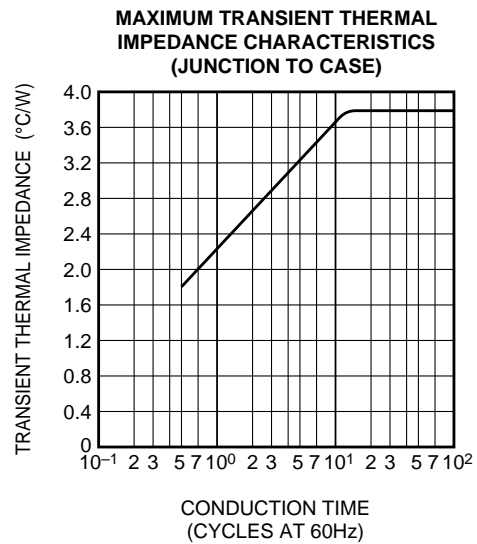
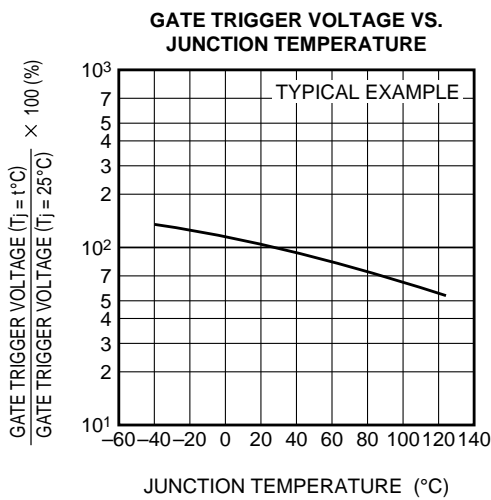
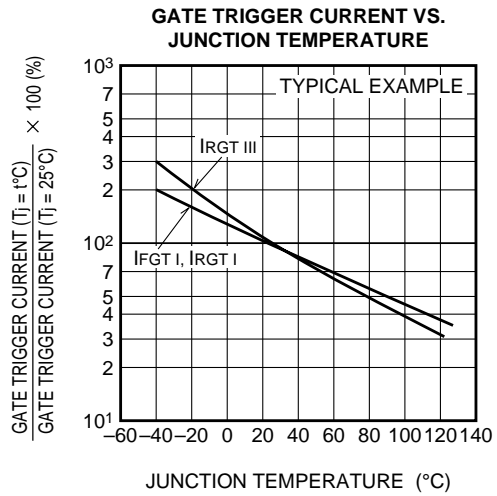
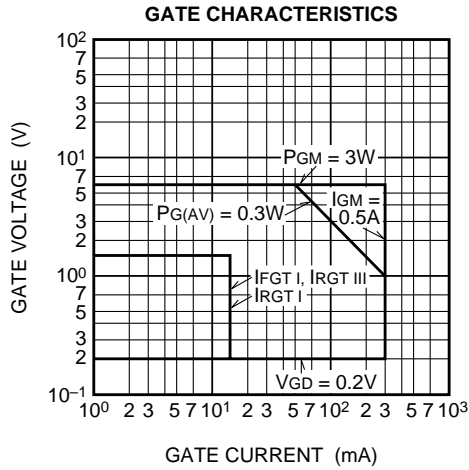


RATED SURGE ON-STATE CURRENT



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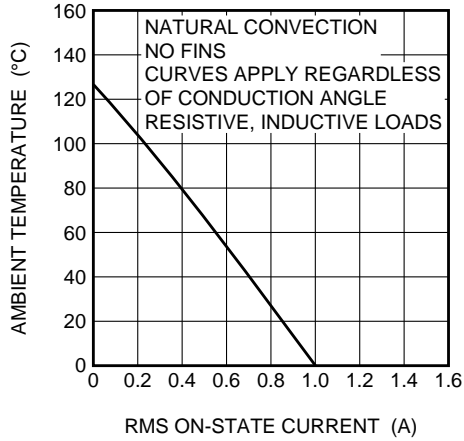
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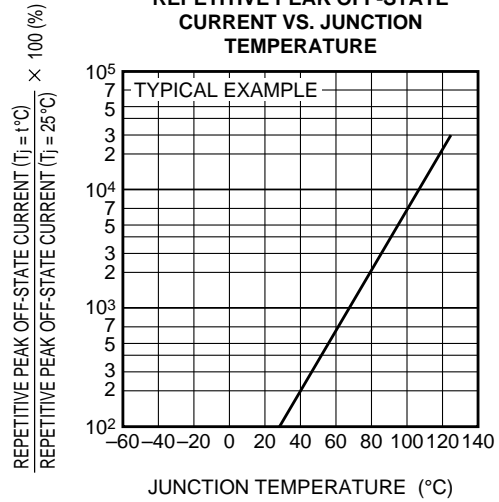
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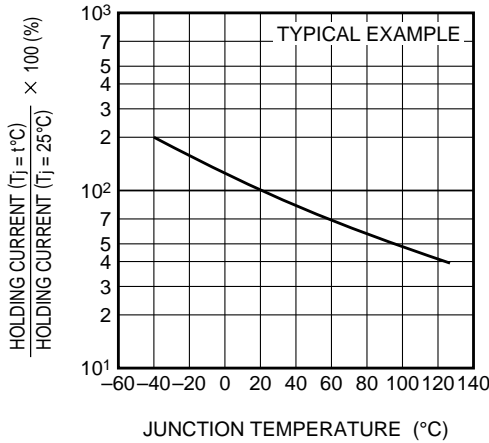
**ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT**



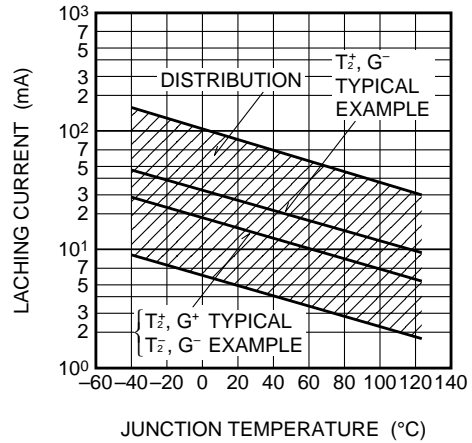
**REPETITIVE PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE**



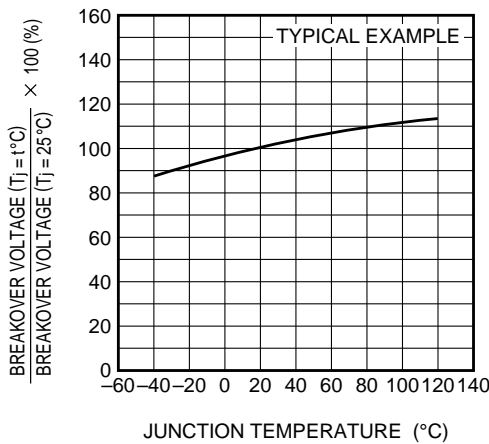
**HOLDING CURRENT VS. JUNCTION TEMPERATURE**



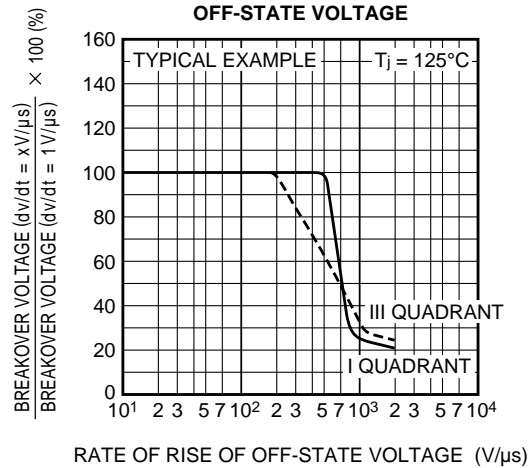
**LATCHING CURRENT VS. JUNCTION TEMPERATURE**



**BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE**

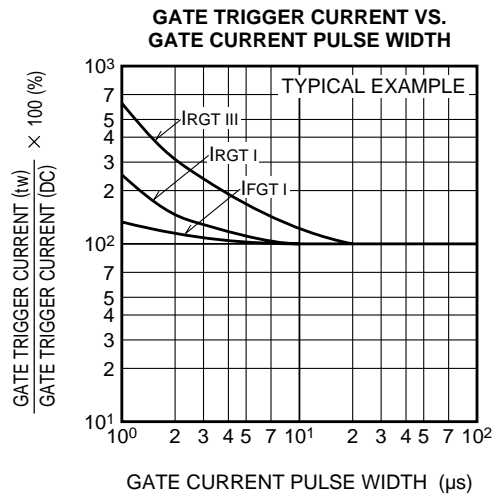
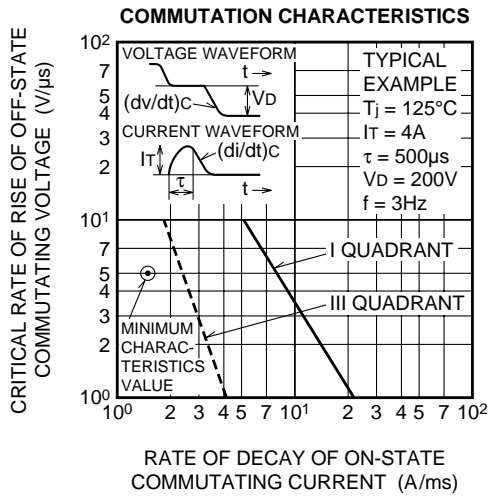


**BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE**



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**GATE TRIGGER CHARACTERISTICS TEST CIRCUITS**

